

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74LCX16374AFT

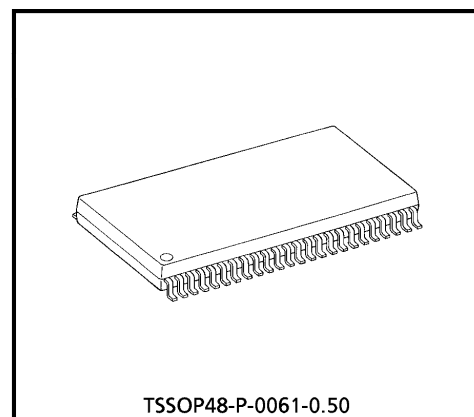
LOW-VOLTAGE 16-BIT D-TYPE FLIP-FLOP WITH 5V TOLERANT INPUTS AND OUTPUTS

The TC74LCX16374AFT is a high performance CMOS 16bit D-TYPE FLIP FLOP. Designed for use in 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

The device is designed for low-voltage (3.3V) V_{CC} applications, but it could be used to interface to 5V supply environment for both inputs and outputs.

This 16-bit D-type flip-flop is controlled by a clock input (CK) and a output enable input ($\overline{OE}$) which are common to each byte. It can be used as two 8-bit flip-flops or one 16-bit flip-flop. When the $\overline{OE}$ input is high, the outputs are in a high impedance state.

All inputs are equipped with protection circuits against static discharge.



Weight : 0.25g (Typ.)

PIN CONNECTION

$\overline{1OE}$	1	48	1CK
1Q1	2	47	1D1
1Q2	3	46	1D2
GND	4	45	GND
1Q3	5	44	1D3
1Q4	6	43	1D4
V_{CC}	7	42	V_{CC}
1Q5	8	41	1D5
1Q6	9	40	1D6
GND	10	39	GND
1Q7	11	38	1D7
1Q8	12	37	1D8
2Q1	13	36	2D1
2Q2	14	35	2D2
GND	15	34	GND
2Q3	16	33	2D3
2Q4	17	32	2D4
V_{CC}	18	31	V_{CC}
2Q5	19	30	2D5
2Q6	20	29	2D6
GND	21	28	GND
2Q7	22	27	2D7
2Q8	23	26	2D8
$\overline{2OE}$	24	25	2CK

(TOP VIEW)

961001EBA2

● TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

TRUTH TABLE

INPUT			OUTPUT
$\overline{1OE}$	1CK	1D1-1D8	1Q1-1Q8
H	X	X	Z
L		X	Qn
L		L	L
L		H	H

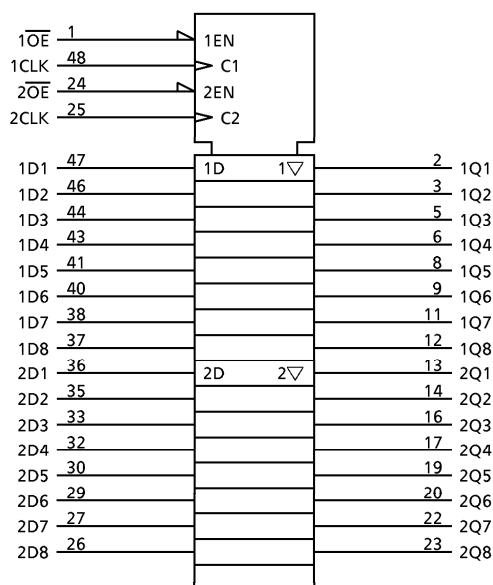
INPUT			OUTPUT
$\overline{2OE}$	2CK	2D1-2D8	2Q1-2Q8
H	X	X	Z
L		X	Qn
L		L	L
L		H	H

X : Don't Care

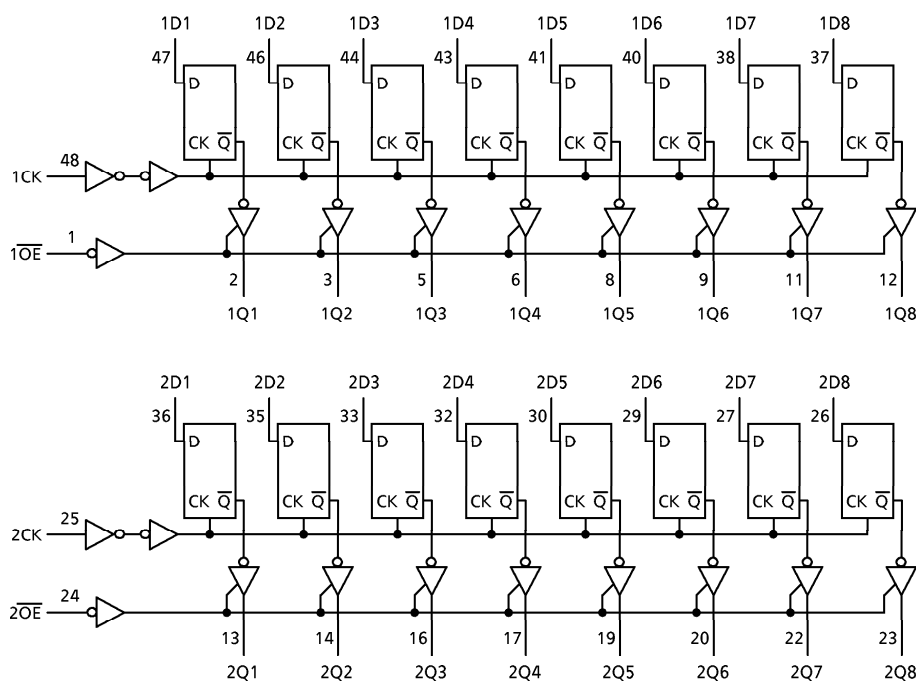
Z : High impedance

Qn : No change

IEC LOGIC SYMBOL



SYSTEM DIAGRAM



961001EBA2'

- The products described in this document are subject to foreign exchange and foreign trade control laws.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.

MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Power Supply Voltage	V_{CC}	- 0.5~7.0	V
Input Voltage	V_{IN}	- 0.5~7.0	V
Output Voltage	V_{OUT}	- 0.5~7.0 (Note 1) - 0.5~ $V_{CC} + 0.5$ (Note 2)	V
Input Diode Current	I_{IK}	- 50	mA
Output Diode Current	I_{OK}	± 50 (Note 3)	mA
DC Output Current	I_{OUT}	± 50	mA
Power Dissipation	P_D	400	mW
DC V_{CC} / Ground Current Per Supply Pin	I_{CC} / I_{GND}	± 100	mA
Storage Temperature	T_{stg}	- 65~150	°C

(Note 1) Output in Off-State

(Note 2) High or Low State. I_{OUT} absolute maximum rating must be observed.(Note 3) $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

RECOMMENDED OPERATING RANGE

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	2.0~3.6 1.5~3.6 (Note 4)	V
Input Voltage	V_{IN}	0~5.5	V
Output Voltage	V_{OUT}	0~5.5 (Note 5) 0~ V_{CC} (Note 6)	V
Output Current	I_{OH} / I_{OL}	± 24 (Note 7) ± 12 (Note 8)	mA
Operating Temperature	T_{opr}	- 40~85	°C
Input Rise And Fall Time	dt / dv	0~10 (Note 9)	ns / V

(Note 4) Data Retention Only

(Note 5) Output in Off-State

(Note 6) High or Low State

(Note 7) $V_{CC} = 3.0 \sim 3.6V$ (Note 8) $V_{CC} = 2.7 \sim 3.0V$ (Note 9) $V_{IN} = 0.8 \sim 2.0V$, $V_{CC} = 3.0V$

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = -40~85°C)

PARAMETER		SYMBOL	TEST CONDITION		V _{CC} (V)	MIN.	MAX.	UNIT
Input Voltage	"H" Level	V _{IH}			2.7~3.6	2.0	—	V
	"L" Level	V _{IL}			2.7~3.6	—	0.8	V
Output Voltage	"H" Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = - 100μA	2.7~3.6	V _{CC} - 0.2	—	V
				I _{OH} = - 12μA	2.7	2.2	—	
				I _{OH} = - 18mA	3.0	2.4	—	
				I _{OH} = - 24mA	3.0	2.2	—	
	"L" Level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100μA	2.7~3.6	—	0.2	V
				I _{OL} = 12mA	2.7	—	0.4	
				I _{OL} = 16mA	3.0	—	0.4	
				I _{OL} = 24mA	3.0	—	0.55	
Input Leakage Current		I _{IN}	V _{IN} = 0~5.5V	2.7~3.6	—	± 5.0	μA	
3-State Output Off-State Current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~5.5V	2.7~3.6	—	± 5.0	μA	
Power Off Leakage Current		I _{OFF}	V _{IN} / V _{OUT} = 5.5V	0	—	10.0	μA	
Quiescent Supply Current		I _{CC}	V _{IN} = V _{CC} or GND	2.7~3.6	—	20.0	μA	
			V _{IN} / V _{OUT} = 3.6~5.5V	2.7~3.6	—	± 20.0		
Increase In I _{CC} Per Input		ΔI _{CC}	V _{IH} = V _{CC} - 0.6V	2.7~3.6	—	500	μA	

AC characteristics (Ta = -40~85°C)

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	MIN.	MAX.	UNIT
Maximum Clock Frequency	f _{MAX}	(Fig.1, 2)	2.7	—	—	MHz
			3.3 ± 0.3	170	—	
Propagation Delay Time (CK - Q)	t _{pLH} t _{pHL}	(Fig.1, 2)	2.7	—	8.0	ns
			3.3 ± 0.3	1.5	7.0	
3-State Output Enable Time	t _{pZL} t _{pZH}	(Fig.1, 3)	2.7	—	8.2	ns
			3.3 ± 0.3	1.5	7.2	
3-State Output Disable Time	t _{pLZ} t _{pHZ}	(Fig.1, 3)	2.7	—	8.2	ns
			3.3 ± 0.3	1.5	7.2	
Minimum Pulse Width (CK)	t _w (H) t _w (L)	(Fig.1, 2)	2.7	4.0	—	ns
			3.3 ± 0.3	3.0	—	
Minimum Set-up Time	t _s	(Fig.1, 2)	2.7	2.5	—	ns
			3.3 ± 0.3	2.5	—	
Minimum Hold Time	t _h	(Fig.1, 2)	2.7	1.5	—	ns
			3.3 ± 0.3	1.5	—	
Output To Output Skew	t _{osLH} t _{osHL}	(Note 10)	2.7	—	—	ns
			3.3 ± 0.3	—	1.0	

(Note 10) Parameter guaranteed by design.

$$(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$$

Dynamic switching characteristics

(Ta = 25°C, Input t_r = t_f = 2.5ns, C_L = 50pF, R_L = 500Ω)

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	TYP	UNIT
Quiet Output Maximum Dynamic V _{OL}	V _{OLP}	V _{IH} = 3.3V, V _{IL} = 0V	3.3	0.8	V
Quiet Output Minimum Dynamic V _{OL}	V _{OLV}	V _{IH} = 3.3V, V _{IL} = 0V	3.3	0.8	V

Capacitive characteristics (Ta = 25°C)

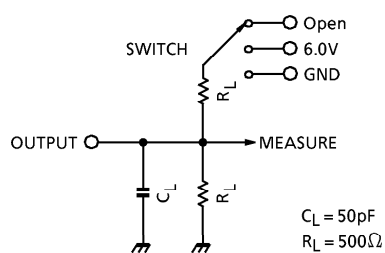
PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	TYP	UNIT
Input Capacitance	C _{IN}	—	3.3	7	pF
Output Capacitance	C _{OUT}		3.3	8	pF
Power Dissipation Capacitance	C _{PD}	f _{IN} = 10MHz (Note 11)	3.3	25	pF

(Note 11) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC(opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 16. \text{ (Per bit)}$$

Fig.1 Test circuit



PARAMETER	SWITCH
t_{pLH} , t_{pHL}	Open
t_{pLZ} , t_{pZL}	6.0V
t_{pHZ} , t_{pZH}	GND
t_w , t_s , t_h , f_{MAX}	Open

AC WAVEFORM

Fig.2 t_{pLH} , t_{pHL} , t_w , t_s , t_h

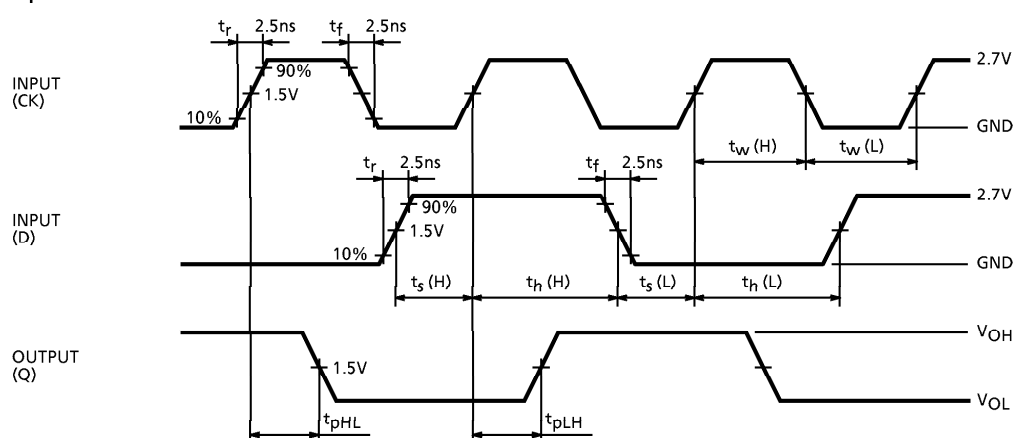
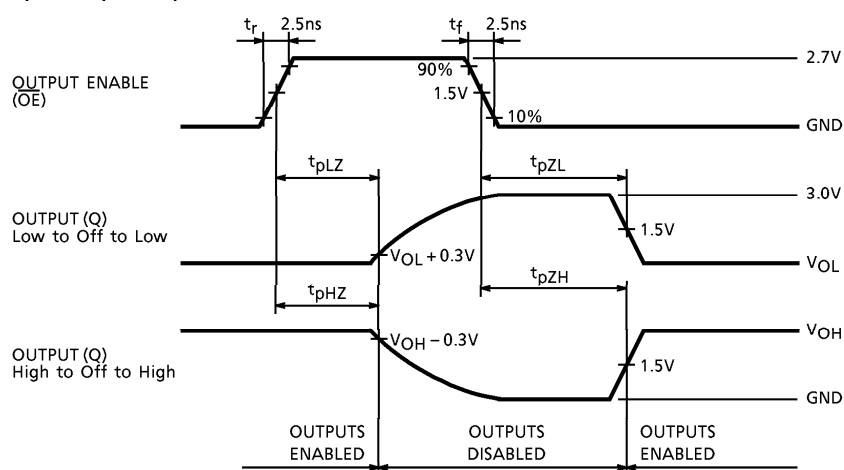


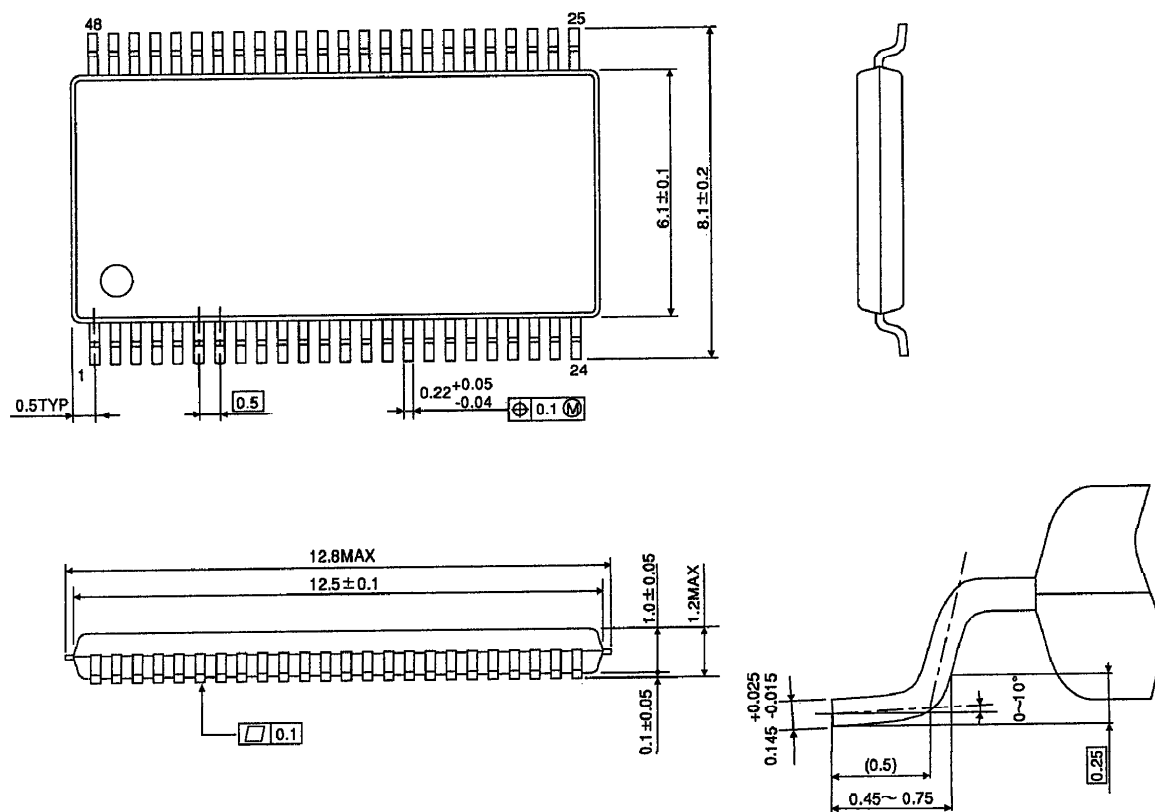
Fig.3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}



OUTLINE DRAWING

TSSOP48-P-0061-0.50

Unit : mm



Weight : 0.25g (Typ.)